





**Pin Definition:** 

1. Gate 2. Source 3. Drain

### **PRODUCT SUMMARY**

V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ)	I <sub>D</sub> (A)
-20	55 @ V <sub>GS</sub> = -4.5V	-4.0
	85 @ V <sub>GS</sub> = -2.5V	-2.5

### Features

- Advance Trench Process Technology •
- High Density Cell Design for Ultra Low On-resistance •

### **Application**

- Load Switch •
- PA Switch

### **Ordering Information**

Part No.	Package	Packing
TSM2311CX RFG	SOT-23	3Kpcs / 7" Reel

Note: "G" denotes Halogen Free Product.

#### Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	-20	V	
Gate-Source Voltage		V <sub>GS</sub>	±8	V	
Continuous Drain Current, V <sub>GS</sub> @ 4.5V.		I <sub>D</sub>	-4	А	
Pulsed Drain Current, V <sub>GS</sub> @ 4.5V		I <sub>DM</sub>	-20	А	
Continuous Source Current (Diode Conduction) <sup>a,b</sup>		I <sub>S</sub>	-0.72	А	
Maximum David Diasis ation	Ta = 25°C	5	0.9	147	
Maximum Power Dissipation	Ta = 75°C	P <sub>D</sub>	0.57	W	
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C	

### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Lead Temperature (1/8" from case)	TL	5	S
Junction to Ambient Thermal Resistance (PCB mounted)	RƏ <sub>JA</sub>	250	°C/W

#### Notes:

a. Pulse width limited by the Maximum junction temperature

b. Surface Mounted on FR4 Board,  $t \le 5$  sec.

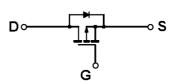
c. Surface Mounted on FR4 Board,

VDS(V)	$\pi_{DS(on)}(11122)$	I <sub>D</sub> (A)
22	55 @ V <sub>GS</sub> = -4.5V	-4.0
-20	85 @ V <sub>GS</sub> = -2.5V	-2.5

**TSM2311** 

20V P-Channel MOSFET

# **Block Diagram**



P-Channel MOSFET



## Electrical Specifications (Ta = 25°C unless otherwise noted)

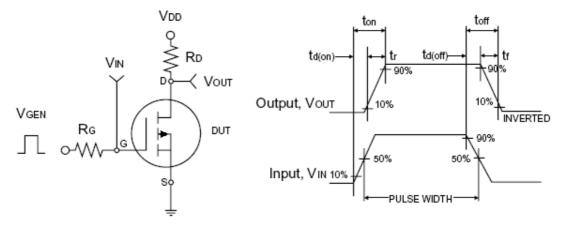
Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = -250uA$	BV <sub>DSS</sub>	-20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	V <sub>GS(TH)</sub>	-0.6		-1.4	V
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS}$ = -16V, $V_{GS}$ = 0V	I <sub>DSS</sub>			-1.0	μA
On-State Drain Current <sup>a</sup>	$V_{DS} \ge -10V, V_{GS} = -5V$	I <sub>D(ON)</sub>	-6			А
Drain-Source On-State	$V_{GS} = -4.5V, I_{D} = -4A$			45	55	
Resistance <sup>a</sup>	$V_{GS}$ = -2.5V, $I_{D}$ = -2.5A	$V_{GS} = -2.5V, I_D = -2.5A$ $R_{DS(ON)}$		75	85	mΩ
Forward Transconductance <sup>a</sup>	$V_{DS} = -5V, I_{D} = -4A$	<b>g</b> <sub>fs</sub>		9		S
Diode Forward Voltage	$I_{S}$ = -0.75A, $V_{GS}$ = 0V	$V_{SD}$		- 0.8	-1.2	V
Dynamic <sup>⁵</sup>		_		_	_	
Total Gate Charge		Qg		6	9	
Gate-Source Charge	$V_{DS} = -6V, I_D = -4A,$ $V_{GS} = -4.5V$	$Q_{gs}$		1.4		nC
Gate-Drain Charge	$v_{GS} = -4.5 v$	$Q_{gd}$		1.9		
Input Capacitance		C <sub>iss</sub>		640		
Output Capacitance	$V_{DS} = -6V, V_{GS} = 0V,$ f = 1.0MHz	C <sub>oss</sub>		180		pF
Reverse Transfer Capacitance		C <sub>rss</sub>		90		
Switching <sup>c</sup>						
Turn-On Delay Time		t <sub>d(on)</sub>		22	35	
Turn-On Rise Time	$V_{DD} = -6V, R_L = 6\Omega,$	tr		35	55	
Turn-Off Delay Time	$I_{\rm D} = -1$ A, $V_{\rm GEN} = -4.5$ V,	t <sub>d(off)</sub>		45	70	nS
Turn-Off Fall Time	$R_{G} = 6\Omega$	t <sub>f</sub>		25	50	

#### Notes:

a. pulse test: PW  $\leq$  300µS, duty cycle  $\leq$  2%

b. For DESIGN AID ONLY, not subject to production testing.

b. Switching time is essentially independent of operating temperature.

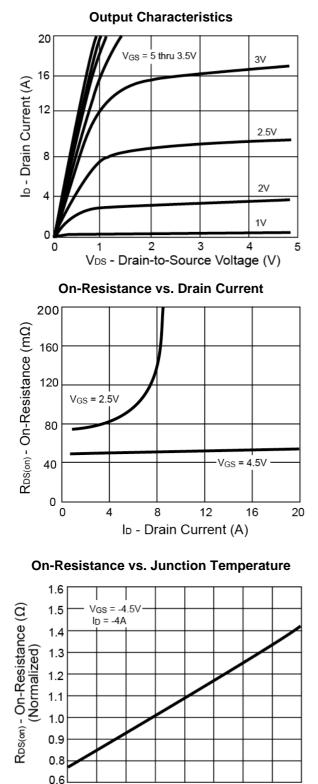


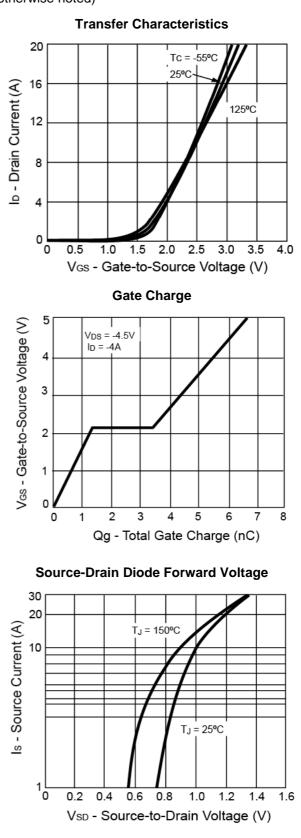
Switching Test Circuit

Switchin Waveforms



### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)





-25

-50

0

25

50

Tj - Junction Temperature (°C)

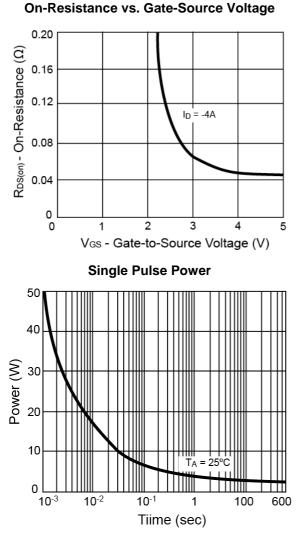
75

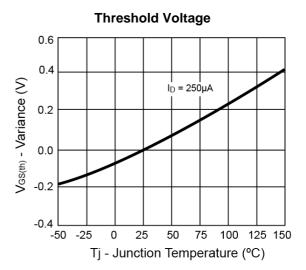
100

125 150

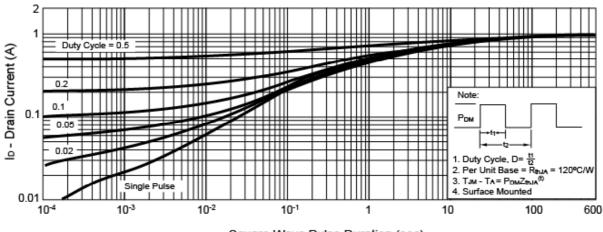


### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)





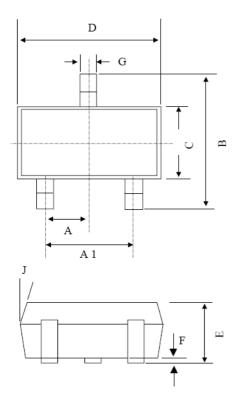
#### Normalized Thermal Transient Impedance, Junction-to-Ambient

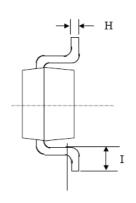


Square Wave Pulse Duration (sec)



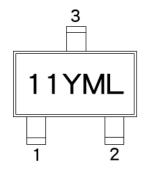
# SOT-23 Mechanical Drawing





SOT-23 DIMENSION				
DIM	MILLIMETERS		INCHES	
DIN	MIN	MAX	MIN	MAX.
Α	0.95 BSC		0.037 BSC	
A1	1.9	BSC	0.074 BSC	
В	2.60	3.00	0.102	0.118
С	1.40	1.70	0.055	0.067
D	2.80	3.10	0.110	0.122
Е	1.00	1.30	0.039	0.051
F	0.00	0.10	0.000	0.004
G	0.35	0.50	0.014	0.020
Н	0.10	0.20	0.004	0.008
I	0.30	0.60	0.012	0.024
J	5°	10º	5°	10º

# **Marking Diagram**



11	= Device	Code
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- Y = Year Code
- M = Month Code for Halogen Free Product

<b>O</b> =Jan	P =Feb	<b>Q</b> =Mar	R =Apr
<b>S</b> =May	<b>T</b> =Jun	U =Jul	V =Aug
W =Sep	X =Oct	Y =Nov	<b>Z</b> =Dec
L = Lot Code			



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